

Sheet 1 of 7

FORM PTO-1449
(REV. 6-89)U.S. DEPARTMENT OF COMMERCE
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Attorney's Docket No.

22920-06460

Serial No.

10/087,408

INFORMATION DISCLOSURE CITATION

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Xiaodong Huang et al.

Filing Date

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FORM PTO-1449 (REV. 6-89)		U.S. DEPARTMENT OF COMMERCE Patent and Trademark Office		Attorney's Office No. 22920-06460	Serial No. 10/087,408
INFORMATION DISCLOSURE CITATION				Applicant Xiaodong Huang et al.	
(Use several sheets if necessary)				Filing Date March 1, 2002	Group Art Unit Unassigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
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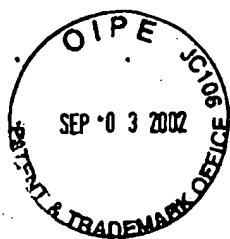
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REV. 02/01

22920/06460/DOCS/1256916.1

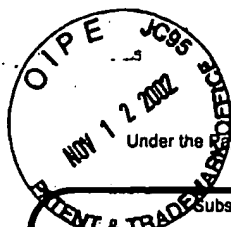


Sheet 7 of 7

FORM PTO-1449 (REV. 6-89)		U.S. DEPARTMENT OF COMMERCE Patent and Trademark Office		Attorney's Docket No. 22920-06460	Serial No. 10/087,408
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant Xiaodong Huang et al.	
				Filing Date March 1, 2002	Group Art Unit Unassigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
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REV: 02/01

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application No.	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2881
Examiner Name	Not yet known
Attorney Docket Number	22920-06460

Sheet	1	of	1
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Examiner Initials*	Cite No. ¹	Document No. Number - Kind Code ² (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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	B	US-5,543,354	08/06/1998	Richard et al.
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OTHER REFERENCES - NON-PATENT LITERATURE DOCUMENTS

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JD	L	U.S. Patent Application Publication, US 2001/0050934, December 13, 2001; Choquette et al.	

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Examiner Signature		Date Considered	2/03/04
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application N .	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2828
Examiner Name	James W. Davie
Attorney Docket Number	22920-06460

Sheet 1 of 2

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Examiner Initials*	Cite No. ¹	Document No. Number - Kind Code ² (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application No.	10/087,408
				Filing Date	March 1, 2002
				First Named Inventor	Xiaodong Huang
				Art Unit	2828
				Examiner Name	James W. Davie
Sheet	2	of	2	Attorney Docket Number	22920-06460

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Examiner Signature		Date Considered	2/03/04
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				Filing Date	March 1, 2002
				First Named Inventor	Xiaodong Huang
				Art Unit	2828
				Examiner Name	James W. Davie
Sheet	1	of	1	Attorney Docket Number	22920-06460

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JD	2	Komori, Kazuhiro et al., "Noise Study of Low-Dimensional Quantum-Well Semiconductor Laser Amplifiers," <i>IEEE Journal of Quantum Electronics</i> , IEEE Inc., New York, US, Vol. 28, No. 9, September 1, 1992, pages 1894-1900.		
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